

Trench IGBT modules

SKiM455GD12T4D1

Preliminary Data

Features

- IGBT 4 = Trenchgate technology
- V_{CE(sat)} with positive temperature coefficient
- · High short circuit capability

Typical Applications*

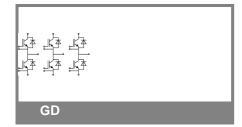
- High Reliability AC inverter drivesUPS

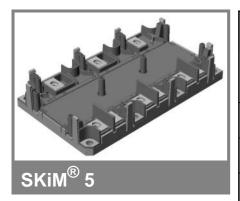
Remarks

- Case temperature limited to T_c = 125°C max
- $T_{j,max}$ of the diode is limited to 150°C

Absolute Maximum Ratings T _c = 25 °C, unless otherwise specified							
Symbol	Conditions		Values	Units			
IGBT							
V_{CES}	$T_j = {^{\circ}C}$		1200	V			
I _C	T _j = 150 °C	T _{heatsink} = 25 °C	400	Α			
		T _{heatsink} = 70 °C	305	Α			
I _{CRM}	I _{CRM} = 3xI _{CNOM}		1350	Α			
V_{GES}			± 20	V			
t _{psc}	V_{CC} = 800 V; $V_{GE} \le 15$ V; VCES < 1200 V	T _j = 150 °C	10	μs			
Inverse Diode							
I _F	T _j = 150 °C	T _{heatsink} = 25 °C	295	Α			
		T _{heatsink} = 70 °C	215	Α			
I _{FRM}	I _{FRM} = 2 x I _{FNOM}		600	Α			
Module							
I _{t(RMS)}				Α			
T _{vj}			-40 + 150	°C			
T _{stg}			-40 +125	°C			
V _{isol}	AC, 1 min.		2500	V			

Characteristics T _c =		25 °C, unless otherwise specified				
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_{C} = 18 \text{ mA}$		5	5,8	6,5	V
I _{CES}	$V_{GE} = 0 V, V_{CE} = V_{CES}$	T _j = 25 °C			5,0	mA
V _{CE0}		T _j = 25 °C		0,8	0,9	V
		T _j = 125 °C		0,7	0,8	V
r _{CE}	V _{GE} = 15 V	T _j = 25°C		2,2	2,4	mΩ
		T _j = 125°C		3,1	3,3	mΩ
V _{CE(sat)}	I _{Cnom} = 450 A, V _{GE} = 15 V			1,8	2	V
		$T_j = 125^{\circ}C_{chiplev.}$		2,1	2,3	V
C _{ies}				27,9		nF
C _{oes}	$V_{CE} = 25, V_{GE} = 0 V$	f = 1 MHz		1,7		nF
C _{res}				1,5		nF
Q_G	$V_{GE} = -8V/+15V$			2600		nC
R_{Gint}	T _j = 25 °C			1,7		Ω
t _{d(on)}				265		ns
t _r E _{on}	$R_{Gon} = 1 \Omega$	V _{CC} = 600V		60		ns
E _{on}	di/dt = 8200 A/μs	I _C = 450A		34		mJ
^t d(off)	$R_{Goff} = 1 \Omega$	T _j = 125 °C		470		ns
t _f	di/dt = 5300 A/μs	$V_{GE} = \pm 15V$		65		ns
E _{off}				40		mJ
$R_{th(j-s)}$	per IGBT			0,14		K/W





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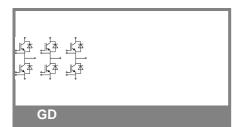
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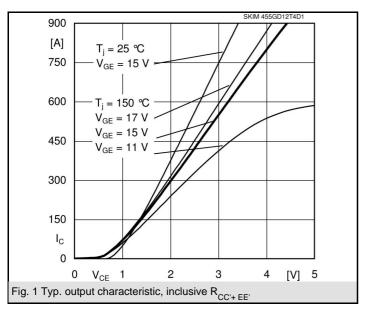
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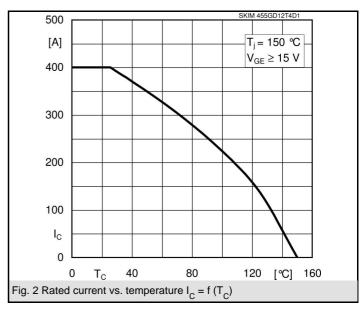
Remarks

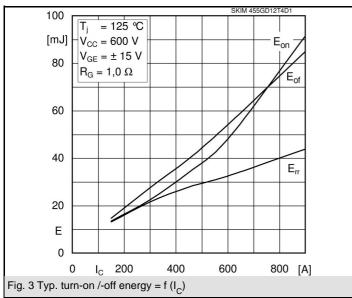
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- $T_{j,max}$ of the diode is limited to 150°C

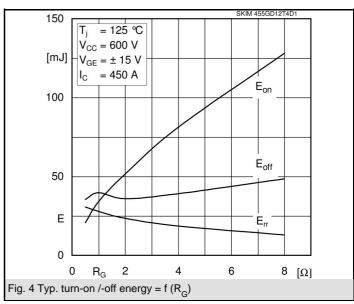
Characteristics								
Symbol	Conditions		min.	typ.	max.	Units		
Inverse Diode								
$V_F = V_{EC}$	I_{Fnom} = 450 A; V_{GE} = 0 V	T _j = 25 °C _{chiplev.}		2,3	2,8	V		
		$T_j = 125 ^{\circ}C_{\text{chiplev.}}$		2,2	2,7	V		
V _{F0}		T _j = 25 °C		1,2	1,6	V		
		T _j = 125 °C		0,9	1,3	V		
r _F		T _j = 25 °C		2,3	2,7	mΩ		
		T _j = 125 °C		2,8	3,1	mΩ		
I _{RRM}	I _F = 450 A	T _i = 125 °C		500		Α		
Q_{rr}	di/dt = 9000 A/µs			64,5		μC		
E _{rr}	V _{GE} = -15V			27,8		mJ		
$R_{th(j-s)}$	per diode			0,19		K/W		
Module								
L _{CE}					20	nΗ		
R _{CC'+EE'}	res., terminal-chip	T _{case} = 25 °C		0,9		mΩ		
		T _{case} = 125 °C		1,1		mΩ		
M _s	to heat sink M5					Nm		
M _t	to terminals M6		4		5	Nm		
w					460	g		
Temperature sensor								
R _{TS}	T = 25 (100)°C			1 (1,67)		kΩ		
Tolerance	T = 25 (100)°C			3 (2)		%		

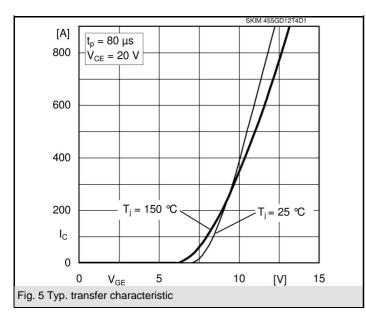


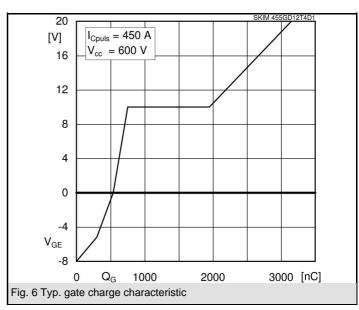


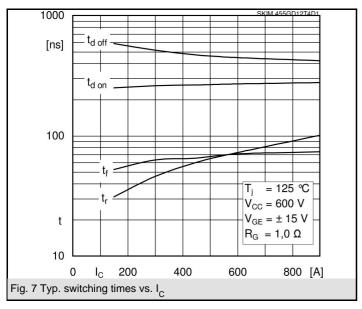


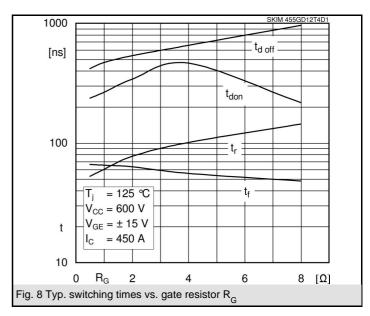


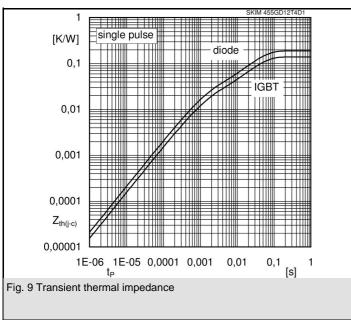


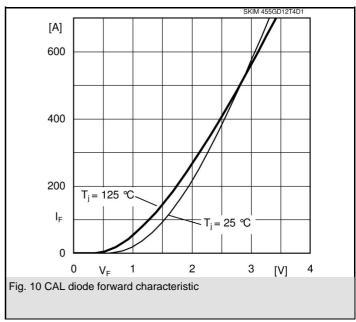


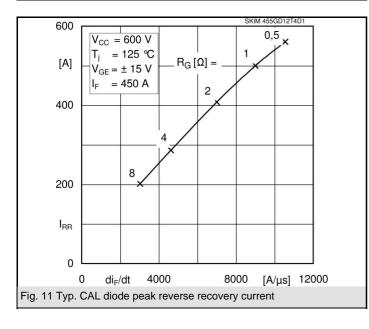


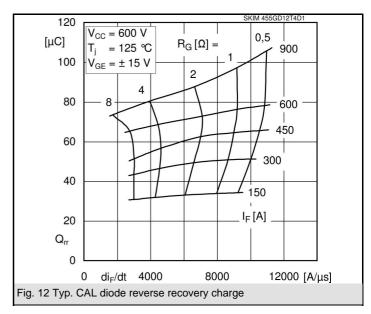


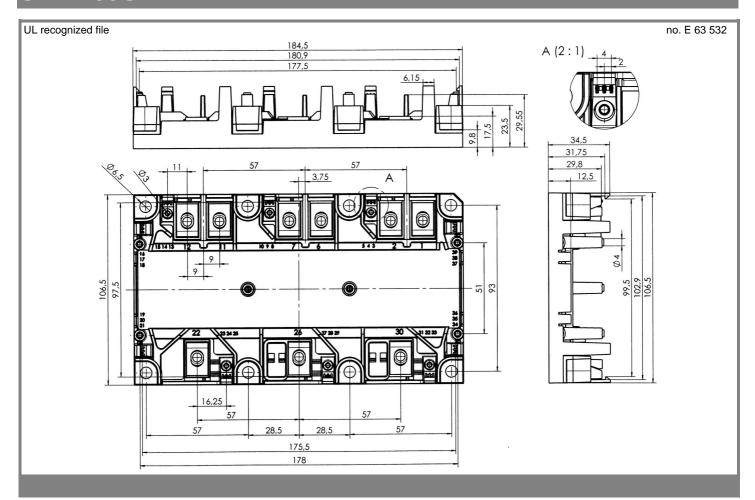


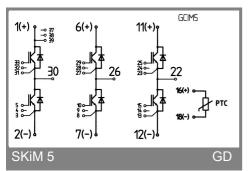












This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

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